

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **Mizuhisa NIHEI, et al.**

Serial Number: **Not Yet Assigned**

Filed: **March 10, 2004**

For: **SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF**

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

March 10, 2004

Sir:

In compliance with 37 CFR 1.56, Applicants call to the attention of the Patent and Trademark Office the references listed on the attached PTO-1449.

A copy of each of the references is enclosed herewith.

In the event there are any fees due in connection with the filing of this paper, please charge Deposit Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, KRATZ, QUINTOS,
HANSON & BROOKS, LLP



Donald W. Hanson
Attorney for Applicants
Reg. No. 27,133

DWH/jaz
Atty. Docket No. **040102**
Suite 1000
1725 K Street, N.W.
Washington, D.C. 20006
(202) 659-2930



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PATENT TRADEMARK OFFICE

Enclosures: PTO-1449; References (7)

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 040102	Serial No. New Application
	Applicant(s): Mizuhisa NIHEI, et al.	
	Filing Date: March 10, 2004	Group Art Unit: Not Yet Assigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA	6,303,094	M. Kusunoki, et al.	10/16/01		
_____	AB	6,278,231	T. Iwasaki, et al.	08/21/01		
_____	AC					
_____	AD					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)	
_____	AE	10-265208	10/06/98	Japan	Yes-Abstract/Corresponds to USP 6303094/Discussed in the specification
_____	AF	2000-31462	01/28/00	Japan	Yes-Abstract/Corresponds to USP 6278231/Discussed in the specification
_____	AG				

OTHER DOCUMENTS

_____	AH	P.P. Ruden, et al.; "Extrinsic Performance Limitations of AlGaIn/GaN Heterostructure Field Effect Transistors"; <i>MRS Internet J. Nitride Semicond. Res.</i> ; 4S1, G6.35; 1999 (6 pages.)/Discussed in the specification		
_____	AI	P. Kim, et al.; "Thermal Transport Measurements of Individual Multiwalled Nanotubes"; <i>Physical Review Letters</i> 87; 215502; November 19, 2001./Discussed in the specification		
_____	AJ	M. Kusunoki, et al.; "A formation mechanism of carbon nanotube films on SiC(0001); <i>Applied Physics Letters</i> ; Vol. 77; Issue 4; July 24, 2000; p. 531./Discussed in the specification		
<table border="1" style="width: 100%;"> <tr> <td style="width: 50%;">Examiner</td> <td style="width: 50%;">Date Considered</td> </tr> </table>			Examiner	Date Considered
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